

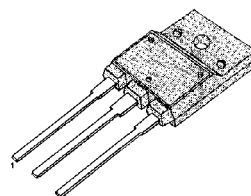
KSC5088**NPN TRIPLE DIFFUSED
PLANAR SILICON TRANSISTOR****HIGH DEFINITION COLOR DISPLAY
HORIZONTAL DEFLECTION OUTPUT
(WITHOUT DAMPER DIODE)**

- High Collector -Base Voltage ($V_{CBO}=1500V$)
- High Speed Switching ($t_f(\text{typ}) = 0.1 \mu s$)

ABSOLUTE MAXIMUM RATING

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	1500	V
Collector Emitter Voltage	V_{CEO}	800	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	8	A
Collector Current (Pulse)	I_C	15	A
Base Current	I_B	4	A
Collector Dissipation ($T_C=25^\circ C$)	P_C	50	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55 ~ 150	$^\circ C$

TO-3PF



1. Base 2. Collector 3. Emitter

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=800V, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4V, I_C=0$			1	mA
DC Current Gain	h_{FE1}	$V_{CE}=5V, I_C=1A$	8			
	h_{FE2}	$V_{CE}=5V, I_C=6A$	5			
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=6A, I_B=1.5A$			5.0	V
Base Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=6A, I_B=1.5A$			1.5	V
Current-Gain Bandwidth Product	f_T	$V_{CE}=10V, I_C=1A$		3		MHz
Storage Time	t_{STG}	$V_{CC}=200V, I_C=6A$			3.0	μs
Fall Time	t_F	$I_{B1}=1.2A, I_{B2}=-2.4A$			0.2	μs

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta \text{ jC}}$	2.49	$^\circ C/W$

